

MT3S106FS

VCO OSCILLETOR STAGE

VHF-UHF Low Noise Amplifier Application

FEATURES

- Low Noise Figure :NF=1.2dB (@f=2GHz)
- High Gain:|S_{21e}|²=10dB (@f=2GHz)

Marking



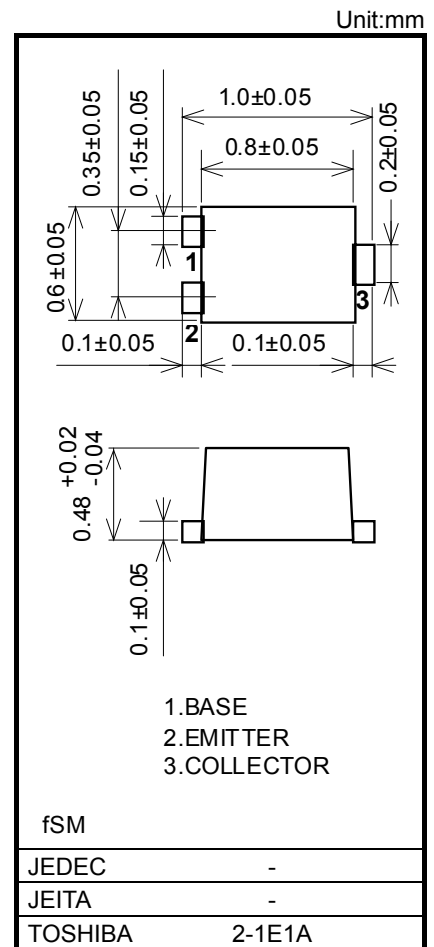
Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-Base voltage	V _{CBO}	13	V
Collector-Emitter voltage	V _{CEO}	6	V
Emitter-Base voltage	V _{EBO}	1	V
Collector-Current	I _C	80	mA
Base-Current	I _B	20	mA
Collector Power dissipation	P _C (Note 1)	100	mW
Junction temperature	T _j	150	°C
Storage temperature Range	T _{stg}	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Device mounted on a glass-epoxy PCB(1.0 cm² x 1.0 mm (t))



Weight: 0.0006 g

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition Frequency	f _T	V _{CE} =1V, I _C =10mA	6.5	8.5	-	GHz
Insertion Gain	S _{21e} ² (1)	V _{CE} =1V, I _C =10mA, f=2GHz	-	8	-	dB
	S _{21e} ² (2)	V _{CE} =3V, I _C =20mA, f=2GHz	8.5	10	-	dB
Noise Figure	NF	V _{CE} =1V, I _C =10mA, f=2GHz	-	1.2	2	dB

Electrical Characteristics (Ta = 25°C)

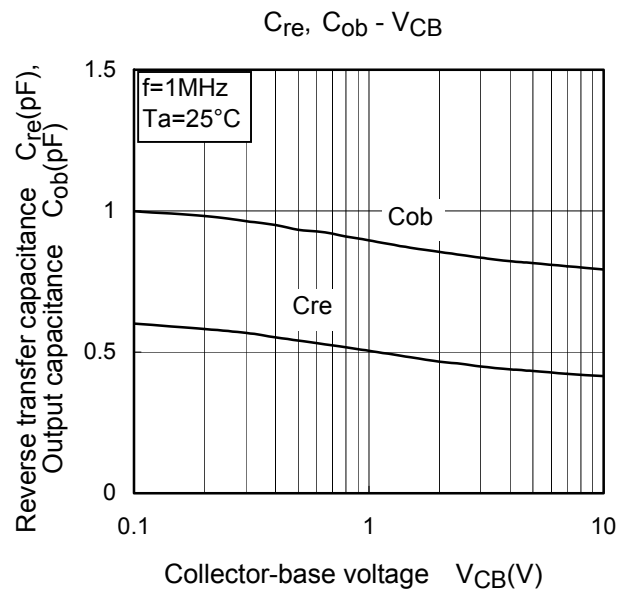
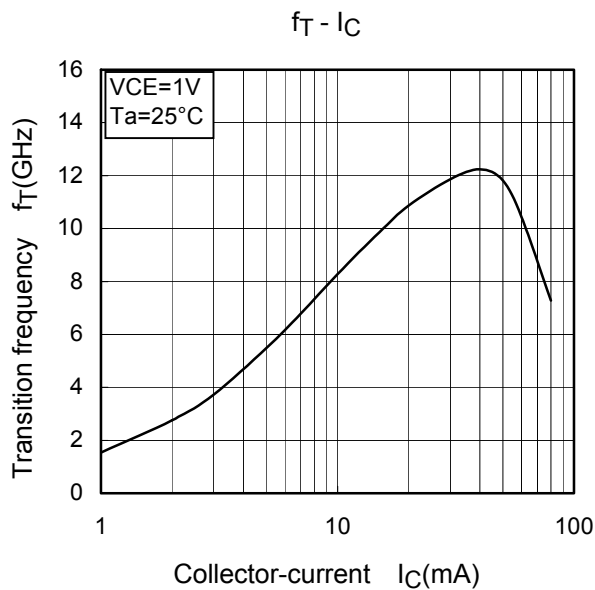
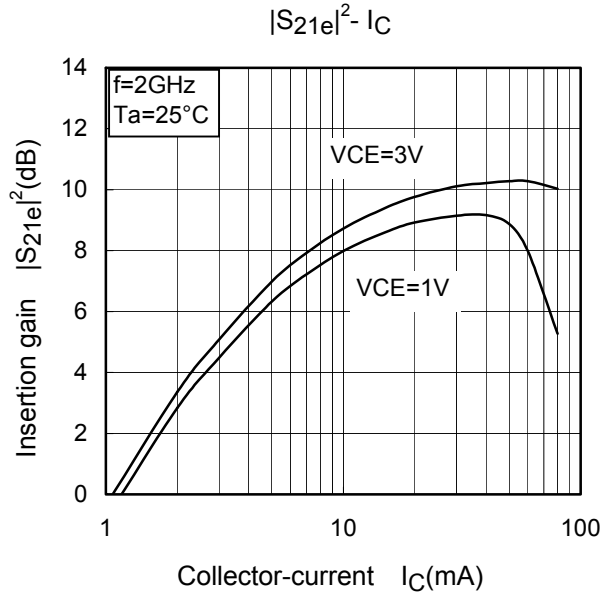
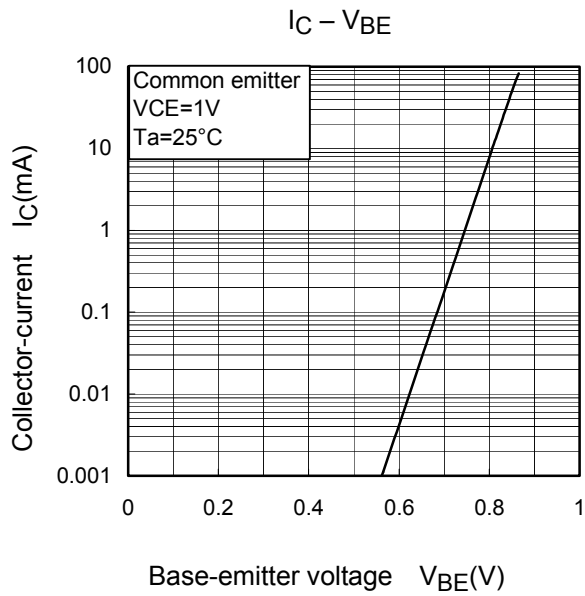
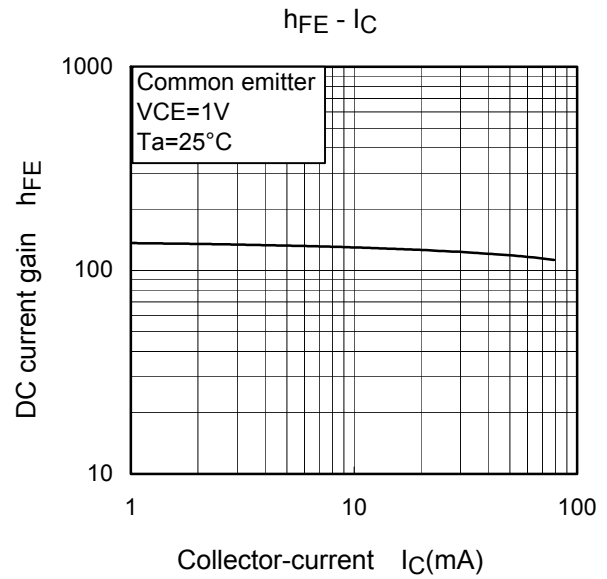
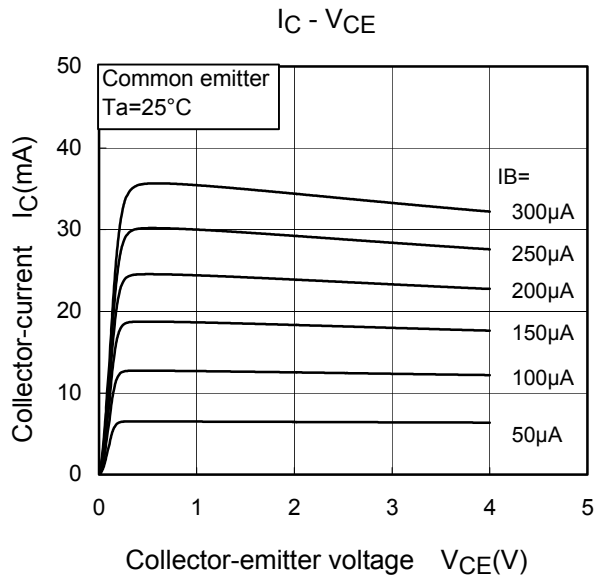
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} =5V, I _E =0	-	-	0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =1V, I _C =0	-	-	0.5	μA
DC Current Gain	h _{FE}	V _{CE} =1V, I _C =5mA	110	-	160	-
Reverse Transistor Capacitance	C _{re}	V _{CB} =1V, I _E =0, f=1MHz (Note)	-	0.5	0.7	pF

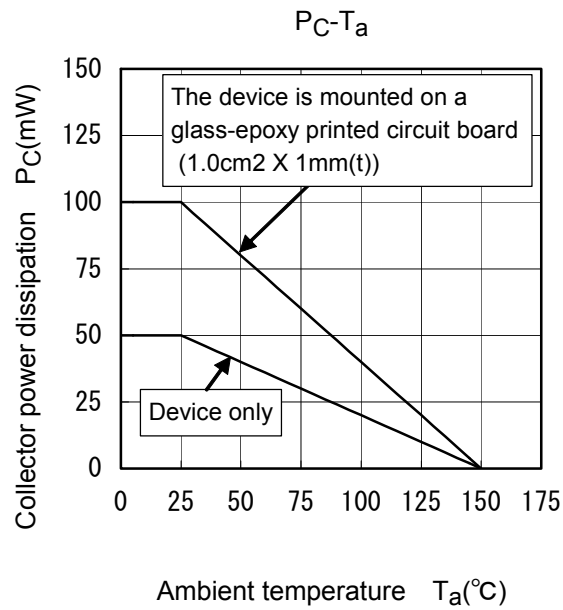
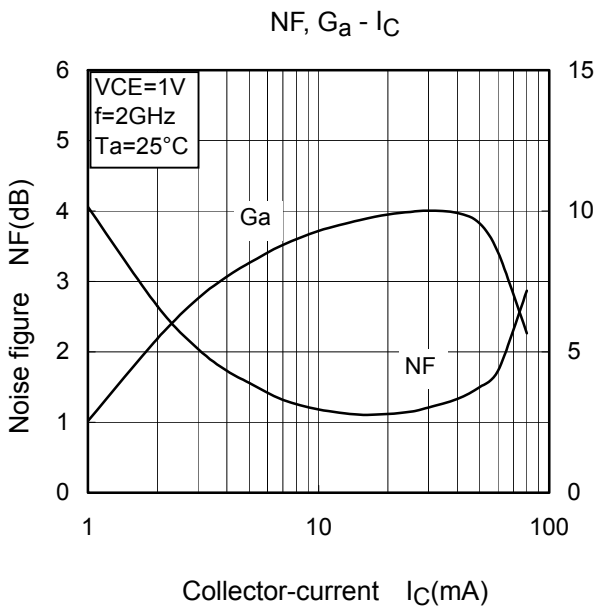
Note : C_{re} is measured by 3 terminal method with capacitance Bridge.

Caution:

This device is sensitive to electrostatic discharge due to applied the high frequency transistor process of f_T=60GHz class is used for this product.

Please make enough tool and equipment earthed when you handle.





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20070701-EN GENERAL

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